Dependence of VO$_2$ thin-film metal-insulator transition on its intrinsic impurities

CHANGHONG CHEN$^1$, YONG ZHAO, ZHAOYANG FAN, Nano Tech Center and Department of Electrical and Computer Engineering, Texas Tech University — We present variation in strain, metal-insulator transition temperature ($T_{MIT}$), activation energy ($\Delta E_a$), and charge carrier type in the insulating phase of (011) preferred polycrystalline (Poly-) and multidomain (020) epitaxial (Epi-) VO$_2$ films grown at different temperature ($T_S$), to produce variable intrinsic impurities. Both the Poly- and Epi-VO$_2$ behave $n$-type conductivity when grown at relative low $T_S$. As $T_S$ increases, acceptor density of impurity increases to alter conductivity from $n$- to $p$-type in the Poly-VO$_2$, while conductive $n$-type still keeps in the Epi-VO$_2$ with increased donor density. Moreover, the strain along monoclinic $a_m$ axis dramatically reverses from tensile to compressive in both the Poly- (848 K $< T_S < 873$ K) and Epi-VO$_2$ (873 K $< T_S < 898$ K), and eventually tend to relaxation again in the Poly-VO$_2$ ($T_S \geq 898$ K) in particular. Consequently, $T_{MIT}$ decreases with increasing the carrier density independent of the conductive type, and low-temperature $\Delta E_a$ is associated with the strain. The larger strain leads to higher $\Delta E_a$, while the relaxed strain produces saturated or the minimum $\Delta E_a$ in the Poly- or Epi-VO$_2$.

$^1$Wuhan National Laboratory for Optoelectronics, Huazhong University of Science and Technology

Zhaoyang Fan
Nano Tech Center and Department of Electrical and Computer Engineering, Texas Tech University

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